

PATENT APPLICATION

Sheet 1 of 9

<p>FORM PTO-1449</p> <p>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</p> <p>(Use several sheets if necessary)</p>	<p>ATTY. DOCKET NO. 200315134-1</p>	<p>APPLICATION NO. 10/799,325</p>	<p>CONFIRMATION NO.</p>
<p>APPLICANT Randy L. Hoffman</p>			
<p>FILING DATE Herewith</p>		<p>GROUP</p>	

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
TT	1A	4,559,238	12/17/2985	Bujatti, et al.	
TT	1B	5,107,314	04/21/1992	Kahng, et al.	
TT	1C	5,744,864	08/28/1998	Cillessen, et al.	
TT	1D	2003/0047785	03/11/2003	Kawasaki, et al.	03/2003
TT	1E	2003/0104859	08/05/2003	Arakawak, et al.	
TT	1F	2003/0111863	06/19/2003	Yagi	
TT	1G	2003/0139028	07/24/2003	Lucovsky	
TT	1H	2003/0180996	09/25/2003	Yamazaki, et al.	
TT	1I	2003/0186489	10/02/2003	Ishikawa	
TT	1J	2003/018221	11/27/2003	Wager, III, et al.	
TT	1K	2003/018222	11/27/2003	Wager, III, et al.	

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FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
TT	1L	WO 97-06544	02/20/1997	Cillessen, et al.		
TT	1M	EP1134811	09/19/2001	Kawasaki, et al.		
	1N					
	1O					
	1P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

TT	1Q	Aoki, Akira, et al., "Tin Oxide Thin Film Transistors", Japan J. Appl. Phys., Vol. 9, p.582 (1970).
TT	1R	Carcia, P.F., et al., "Transparent ZnO thin-film transistor fabricated by rf magnetron sputtering", Applied Physics Letters, Vol. 82, No. 7, pp. 1117-1119 (February 17, 2003).
TT	1S	Carcia, P.F., et al., "ZnO Thin Film Transistors for Flexible Electronics", Mat. Res. Soc. Symp. Proc., Vol. 769, pp. H72.1-H72.6 (2003).

<p>EXAMINER <i>Thien Binh</i></p>	<p>DATE CONSIDERED <i>10-11-2005</i></p>
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PATENT APPLICATION

Sheet 2 of 9

FORM PTO-1449 LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	ATTY. DOCKET NO. 200315134-1	APPLICATION NO. 10/799,325	CONFIRMATION NO.
	APPLICANT Randy L. Hoffman		
	FILING DATE Herewith	GROUP	

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
TT	2A	2003/0224550	12/04/2003	Kokubo, et al.	
TT	2B	60/490,239	07/25/2003		Transparent Thin Film Transistor with Zinc-Tin Oxide Channel...
TT	2C	10/763,239	01/23/2004		Semiconductor Device
TT	2D	10/763,354	01/23/2004		Transistor Including a Deposited Channel Region Having a ...
	2E				
	2F				
	2G				
	2H				
	2I				
	2J				
	2K				

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5/22/07

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	2L					
	2M					
	2N					
	2O					
	2P					

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

TT	2Q	Fu, Shelton, et al., "MOS and MOSFET with Transistion Metal Oxides", SPIE Vol. 2697, pp. 520-527.
TT	2R	Giesbers, J.B., et al., "Dry Etching of All-Oxide Transparent Thin Film Memory Transistors", Microeletronic Engineering, Vol. 35, pp. 71-74 (1997).
TT	2S	Grosse-Holz, K.O., et al. "Semiconductive Behavior of Sb Doped SnO2 Thin Films", Mat. Res. Soc. Symp. Proc., Vol. 401, pp. 67-72 (1998).

EXAMINER

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DATE CONSIDERED

10-11-2005